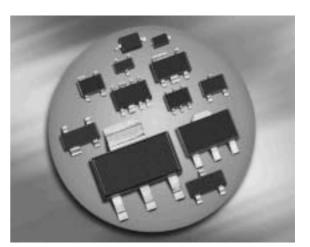


Silicon Switching Diodes

- Switching applications
- High breakdown voltage
- Pb-free (RoHS compliant) package¹⁾
- Qualified according AEC Q101





BAW78D

BAW79D





Туре	Package	Configuration	Marking
BAW78D	SOT89	single	GD
BAW79D	SOT89	common cathode	GH

Maximum Ratings at $T_A = 25^{\circ}$ C, unless otherwise specified

Parameter	Symbol	Value	Unit	
Diode reverse voltage	V _R	400	V	
Peak reverse voltage	V _{RM}	400		
Forward current	/ _F	1	A	
Peak forward current	/ _{FM}	1		
Peak forward current	/ _{FM}	1		
Surge forward current, $t = 1 \ \mu s$	I _{FS}	10		
Non-repetitive peak surge forward current	/ _{FSM}	-		
Total power dissipation	P _{tot}		W	
BAW78D, <i>T</i> _S ≤ 125°C		1		
BAW79D, <i>T</i> _S ≤ 115°C		1		
Junction temperature	Tj	150	°C	
Storage temperature	T _{stg}	-65 150		

¹Pb-containing package may be available upon special request



Thermal Resistance

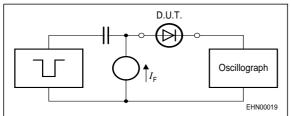
Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R _{thJS}		K/W
BAW78D		≤ 25	
BAW79D		≤ 3 5	

Electrical Characteristics at $T_A = 25^{\circ}$ C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					1
Breakdown voltage	V _(BR)	400	-	-	V
<i>I</i> _(BR) = 100 μA					
Reverse current	l _R	-	-		μA
<i>V</i> _R = 400 V		-	-	1	
$V_{\rm R} = 400 \text{ V}, \ T_{\rm A} = 150 \ ^{\circ}{\rm C}$				50	
Forward voltage	V _F				V
<i>I</i> _F = 1 A		-	-	1.6	
<i>I</i> _F = 2 A		-	-	2	
AC Characteristics					
Diode capacitance	CT	-	10	-	pF
$V_{\rm R} = 0 {\rm V}, f = 1 {\rm MHz}$					
Reverse recovery time	<i>t</i> _{rr}	-	1	-	μs
$I_{\rm F}$ = 200mA, $I_{\rm R}$ = 200mA, measured at $I_{\rm R}$ = 20mA			,		

$$R_{\rm L} = 100\Omega$$

Test circuit for reverse recovery time



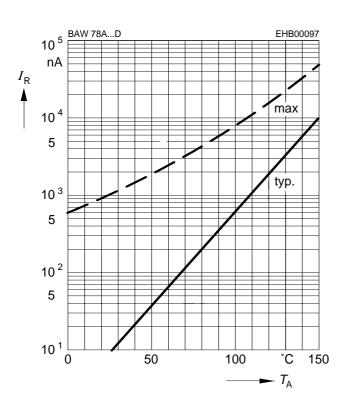
Puls generator: $t_p = 10\mu s$, D = 0.05, $t_r = 0.6ns$, $R_i = 50\Omega$ Oscillograp: $R = 50\Omega$, $t_r = 0.35ns$ $C \le 1pF$

¹For calculation of R_{thJA} please refer to Application Note Thermal Resistance



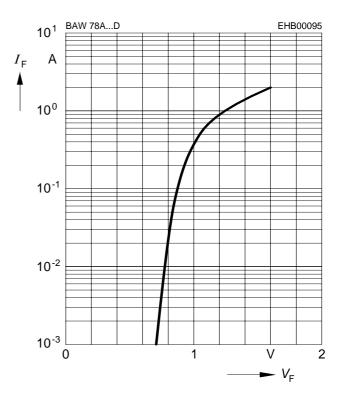
Reverse current $I_{R} = f(T_{A})$

 $V_{\mathsf{R}} = 400\mathsf{V}$

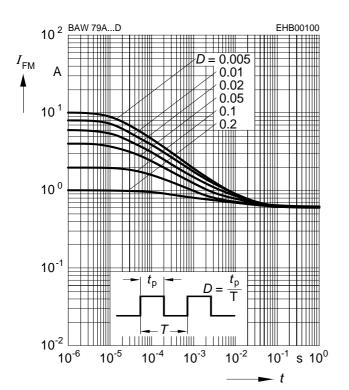


Forward current $I_{\rm F} = f (V_{\rm F})$

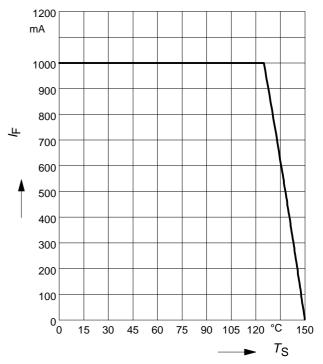
 $T_{\rm A} = 25^{\circ}{\rm C}$



Peak forward current $I_{FM} = f(t_p)$



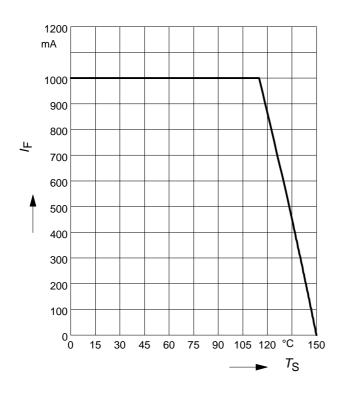
Forward current $I_{\rm F} = f (T_{\rm S})$ BAW78D



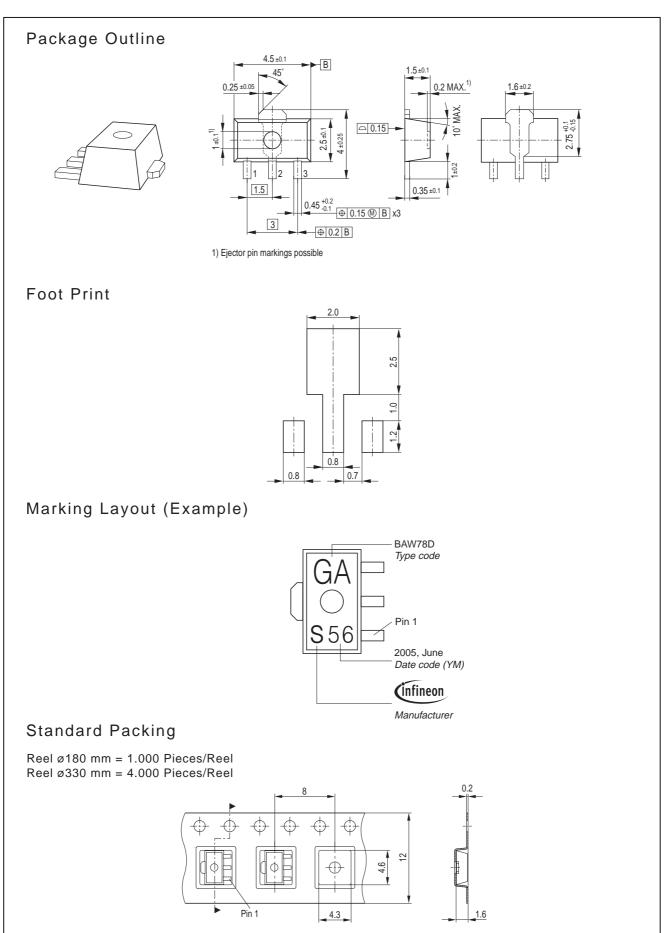


Forward current $I_{\rm F} = f(T_{\rm S})$

BAW79D









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